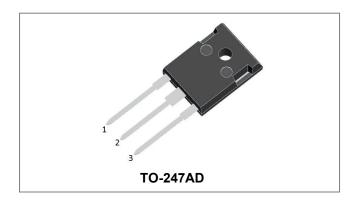


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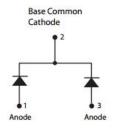
## SDUR60P60WT ULTRAFAST RECTIFIER



## **Applications**

- Antiparallel diode for high frequency switching devices
- Anti saturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating and melting
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

### **Circuit Diagram**



#### **Features**

- Ultra-Fast switching
- High current capability
- Low reverse leakage current
- High surge current capability
- This is a Pb free device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

#### **Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	-	600	V
Average Rectified Forward Current	I <sub>F (AV)</sub>	50% duty cycle @Tc=70°C, rectangular wave form	30(Per Leg) 60(Per Device)	Α
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	I <sub>FSM</sub>	8.3ms, Half Sine pulse	200	А

#### **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop(Per Leg)*	$V_{F1}$	@ 15A, Pulse, T <sub>J</sub> = 25°C @ 30A, Pulse, T <sub>J</sub> = 25°C	1.20 1.50	- 1.70	V
Reverse Current	I <sub>R1</sub>	$@V_R = \text{rated } V_{R, T_J} = 25^{\circ}\text{C}$	0.03	150	uA
(Per Leg)*	I <sub>R2</sub>	@V <sub>R</sub> = rated V <sub>R</sub> , T <sub>J</sub> =125°C	8	1	mA
Reverse Recovery Time (Per Leg)	t <sub>rr</sub>	I <sub>F</sub> =500mA,I <sub>R</sub> =1A,and I <sub>m</sub> =250mA	40	50	ns

<sup>\*</sup> Pulse width < 300 µs, duty cycle < 2%

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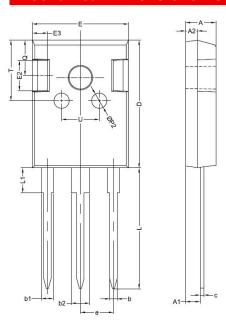


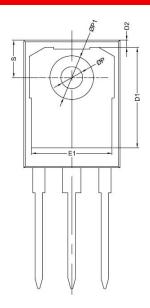


## **Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +175	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +175	°C
Typical Thermal Resistance Junction to Case	R <sub>θ</sub> JC	DC operation	0.34	°C/W
Approximate Weight	wt	-	6.28	g
Case Style	TO-247AD			

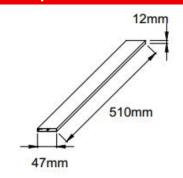
## **Mechanical Dimensions TO-247AD**



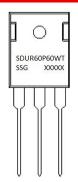


CVMDOL	Millimeters				
SYMBOL	MIN.	TYP.	MAX.		
Α	4.80	5.00	5.20		
A1	2.20	2.41	2.61		
A2	1.90	2.00	2.10		
b	1.10	1.20	1.40		
b1	1.80	2.00	2.20		
b2	2.80	3.00	3.20		
С	0.50	0.60	0.75		
D	20.30	21.00	21.20		
D1		16.55			
D2		1.20			
E	15.45	15.80	16.00		
E1		13.30			
E2		5.00			
E3		2.50			
е		5.44			
L	19.42	19.92	20.70		
L1		4.13			
Р	3.50	3.60	3.70		
P1	7.1		7.40		
P2		2.50			
Q		5.80			
Q S T	6.05	6.15	6.25		
T		10.00			
U		6.20			

## **Tube Specification**



# **Marking Diagram**



Where XXXXX is YYWWL

SDUR = Device Type 60 = Forward Current (60A)

P = P
60 = Reverse Voltage (600V)
WT = Configuration

 SSG
 = SSG

 YY
 = Year

 WW
 = Week

 L
 = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0

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- http://www.smc-diodes.com sales@ smc-diodes.com •

#### SDUR60P60WT



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#### **Ordering Information:**

Device	Package	Shipping	
SDUR60P60WT	TO-247AD(Pb-Free)	25pcs / tube	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

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